**Product data sheet** 

# 1. General description

Dual ultrafast power diode in a SOT78 (TO-220AB) plastic package.

### 2. Features and benefits

- Fast switching
- Low thermal resistance
- High thermal cycling performance
- Very low forward voltage drop
- · High reverse surge capability
- Soft recovery characteristic

# 3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

## 4. Quick reference data

Table 1. Quick reference data

| Symbol               | Parameter                           | rameter Conditions  |     |     |      |      | Unit |
|----------------------|-------------------------------------|---|-----|-----|------|------|------|
| Absolute             | maximum rating                      |   |     |     |      |      |      |
| $V_{RRM}$            | repetitive peak reverse voltage     |   |     | 200 |      |      |      |
| $\mathbf{I}_{F(AV)}$ | average forward current             | δ = 0.5; T <sub>mb</sub> ≤ 114 °C; SQW;<br><u>Fig. 1; Fig. 2; Fig. 3</u>  |     | ,   | 15   |      | А    |
| I <sub>O(AV)</sub>   | average output current              | $\delta$ = 0.5; T <sub>mb</sub> ≤ 114 °C; SQW; both diodes conducting   | 30  |     |      |      | А    |
| I <sub>FSM</sub>     | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode; Fig. 4  | 150 |     |      |      | Α    |
|                      |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode   | 165 |     |      |      | А    |
| $V_{ESD}$            | electrostatic discharge voltage     | HBM; all pins; C =250 pF; R = 1.5 k $\Omega$  | 8   |     |      |      | kV   |
| Symbol               | Parameter                           | Conditions  |     | Min | Тур  | Max  | Unit |
| Static ch            | aracteristics                       |   |     |     |      |      |      |
| V <sub>F</sub>       | forward voltage                     | forward voltage $I_F = 15 \text{ A}; T_j = 25 \text{ °C}; Fig. 6$   |     | -   | 0.95 | 1.05 | V    |
|                      |                                     | I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>   |     | -   | 1    | 1.2  | V    |
|                      |                                     | I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>   |     | -   | 0.78 | 0.85 | V    |
| Dynamic              | characteristics                     |   |     |     |      |      |      |
| t <sub>rr</sub>      | reverse recovery time               | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ - 18 25<br>$T_i = 25 \text{ °C}; \text{ ramp recovery}; Fig. 7$ |     |     |      | 25   | ns   |

**Dual ultrafast power diode** 

# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description            | Simplified outline | Graphic symbol |
|-----|--------|------------------------|--------------------|----------------|
| 1   | A1     | anode 1                | mb                 |                |
| 2   | K      | cathode                |                    | M N M          |
| 3   | A2     | anode 2                |                    | A1 A2          |
| mb  | K      | mounting base; cathode |                    | K<br>sym125    |
|     |        |                        |                    |                |
|     |        |                        |                    |                |
|     |        |                        | 1 2 3              |                |

# 6. Ordering information

**Table 3. Ordering information** 

| Type number | Package  |   |         |  |
|-------------|----------|---|---------|--|
|             | Name     | Description   | Version |  |
| BYQ42E-200  | TO-220AB | plastic single-ended package; heatsink mounted;<br>1 mounting hole; 3-lead TO-220AB | SOT78   |  |

# 7. Marking

### **Table 4. Marking codes**

| Type number | Marking codes |
|-------------|---------------|
| BYQ42E-200  | BYQ42E-200    |

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                           | Conditions  | Values     | Unit |  |  |  |
|--------------------|-------------------------------------|---|------------|------|--|--|--|
| $V_{RRM}$          | repetitive peak reverse voltage     |   | 200        | V    |  |  |  |
| $V_{RWM}$          | crest working reverse voltage       |   | 200        | V    |  |  |  |
| $V_R$              | reverse voltage                     | DC  | 200        | V    |  |  |  |
| I <sub>F(AV)</sub> | average forward current             | $δ = 0.5$ ; $T_{mb} \le 114$ °C; SQW;<br>Fig. 1; Fig. 2; Fig. 3 | 15         | А    |  |  |  |
| I <sub>O(AV)</sub> | average output current              | δ = 0.5; T <sub>mb</sub> ≤ 114 °C; SQW; both diodes conducting  | 30         | Α    |  |  |  |
| I <sub>FSM</sub>   | non-repetitive peak                 | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode; Fig. 4    | 150        | А    |  |  |  |
|                    | forward current                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode           | 165        | А    |  |  |  |
| I <sub>RRM</sub>   | repetitive peak reverse current     | $\delta$ = 0.001; $t_p$ = 2 $\mu$ s                             | 0.2        | Α    |  |  |  |
| I <sub>RSM</sub>   | non-repetitive peak reverse current | t <sub>p</sub> = 100 μs   | 0.2        | А    |  |  |  |
| T <sub>stg</sub>   | storage temperature                 |   | -40 to 150 | °C   |  |  |  |
| T <sub>j</sub>     | junction temperature                |   | 150        | °C   |  |  |  |
| Electrosta         | Electrostatic discharge             |   |            |      |  |  |  |
| V <sub>ESD</sub>   | electrostatic discharge voltage     | HBM; all pins; C = 250 pF; R = 1.5 k $\Omega$                   | 8          | kV   |  |  |  |

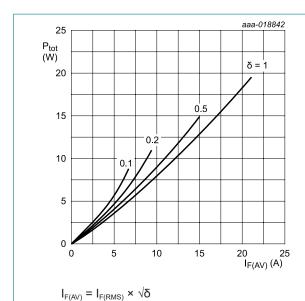
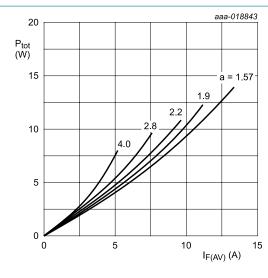


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

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### **Dual ultrafast power diode**

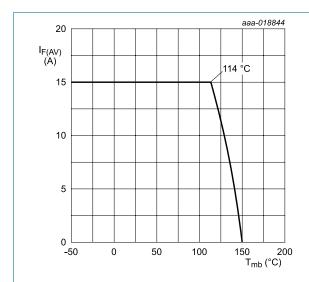


Fig. 3. Average forward current as a function of mounting base temperature; per diode; maximum values

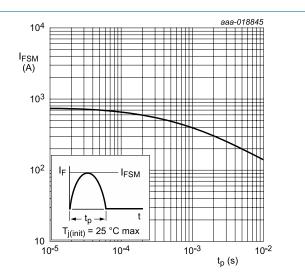


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; per diode; maximum values

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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter  | Conditions  |  | Min | Тур | Max | Unit |
|-----------------------|--|---|--|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance from junction to                        | with heatsink compound;<br>both diodes conducting |  | -   | -   | 1.4 | K/W  |
| mounting base         |  | with heatsink compound;<br>per diode; Fig. 5      |  | -   | -   | 2.4 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient free air |   |  | -   | 60  | -   | K/W  |

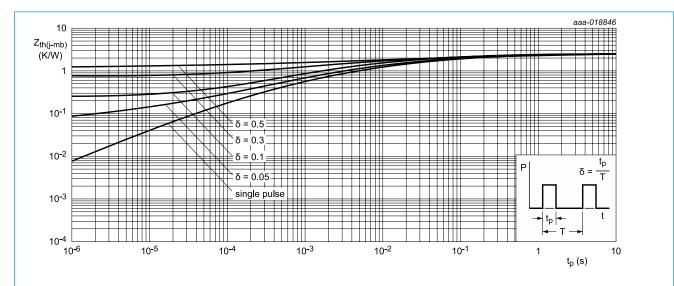
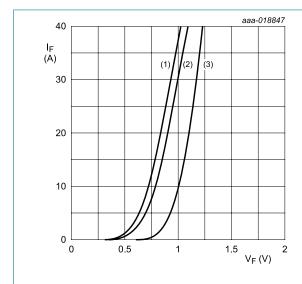


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; per diode; maximum values

## 10. Characteristics

**Table 7. Characteristics** 

|                 | _                             |  |  |     |      |      | T    |
|-----------------|-------------------------------|--|--|-----|------|------|------|
| Symbol          | Parameter                     | Conditions   |  | Min | Тур  | Max  | Unit |
| Static cha      | racteristics                  |  |  |     |      |      |      |
| $V_{F}$         | forward voltage               | I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>  |  | -   | 0.78 | 0.85 | V    |
|                 |                               | I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   |  | -   | 0.95 | 1.05 | V    |
|                 |                               | I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>  |  | -   | 1    | 1.2  | V    |
| I <sub>R</sub>  | reverse current               | rrent V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C   |  | -   | 3    | 20   | μA   |
|                 |                               | V <sub>R</sub> = 200 V; T <sub>j</sub> = 150 °C  |  | -   | 0.3  | 1    | mA   |
| Dynamic         | characteristics               |  |  |     |      |      |      |
| Q <sub>r</sub>  | recovered charge              | $I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$  |  | -   | 6    | 15   | nC   |
|                 |                               | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$ |  | -   | 10   | -    | nC   |
| t <sub>rr</sub> | reverse recovery time         | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$<br>ramp recovery; $T_i = 25 \text{ °C}; Fig. 7$  |  | -   | 18   | 25   | ns   |
| I <sub>RM</sub> | peak reverse recovery current | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$                 |  | -   | 1    | -    | V    |



 $V_{o}$  = 0.712 V;  $R_{s}$  = 0.009  $\Omega$ (1) T<sub>i</sub> = 150 °C; typical values

(2) T<sub>j</sub> = 150 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode

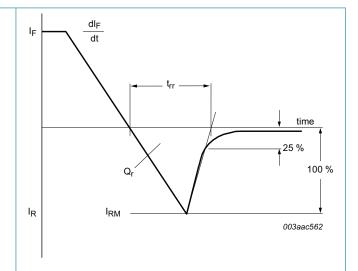


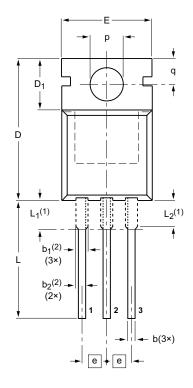
Fig. 7. Reverse recovery definitions; ramp recovery

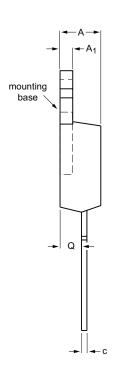
**Dual ultrafast power diode** 

# 11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

**SOT78** 





0 5 10 mm

### **DIMENSIONS** (mm are the original dimensions)

| UNIT | Α          | A <sub>1</sub> | b          | b <sub>1</sub> <sup>(2)</sup> | b <sub>2</sub> <sup>(2)</sup> | С          | D            | D <sub>1</sub> | E           | е    | L            | L <sub>1</sub> <sup>(1)</sup> | L <sub>2</sub> <sup>(1)</sup><br>max. | р          | q          | Q          |
|------|------------|----------------|------------|-------------------------------|-------------------------------|------------|--------------|----------------|-------------|------|--------------|-------------------------------|---------------------------------------|------------|------------|------------|
| mm   | 4.7<br>4.1 | 1.40<br>1.25   | 0.9<br>0.6 | 1.6<br>1.0                    | 1.3<br>1.0                    | 0.7<br>0.4 | 16.0<br>15.2 | 6.6<br>5.9     | 10.3<br>9.7 | 2.54 | 15.0<br>12.8 | 3.30<br>2.79                  | 3.0                                   | 3.8<br>3.5 | 3.0<br>2.7 | 2.6<br>2.2 |

#### Notes

- Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

| OUTLINE |     | REFER           | EUROPEAN | ISSUE DATE |            |                                 |
|---------|-----|-----------------|----------|------------|------------|---------------------------------|
| VERSION | IEC | JEDEC           | JEITA    |            | PROJECTION | ISSUE DATE                      |
| SOT78   |     | 3-lead TO-220AB | SC-46    |            |            | <del>08-04-23</del><br>08-06-13 |

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### **Dual ultrafast power diode**

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| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
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